



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

34/F Amdt  
6/27/02  
R. Welch

In re Application: No. 09/160,657

Docket: UIL-10013C

Filed: September 25, 1998

Group Art Unit 2822

Inventor(s): Joseph W. Lyding et al

Examiner: VOCKRODT, Jeff B.

For: SEMICONDUCTIVE DEVICES AND METHODS FOR SAME

Assistant Commissioner of Patents  
Washington, D.C. 20231

**CERTIFICATE UNDER RULE 37 CFR 1.10**

I hereby certify, that this document and the documents referred to as enclosed therein are being deposited with the United States Postal Service on the date indicated below, in an envelope as "Express Mail Post Office to Addressee: Mailing Label Number ET615589094US addressed to: Assistant Commissioner of Patents, Washington, D.C. 20231.

June 12, 2002 *N. Rhys Merrett*  
Date N. Rhys Merrett

**Amendment under 37 CFR 111**

Dear Sir:

This response to the Office Action mailed December 20, 2001 as supplemented by the Interview Summary mailed February 27, 2002 is accompanied a petition to extend the response period by three months until June 20, 2002.

Please amend the application as follows:

**In the claims:**

Please amend the following claims to read as shown:

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Sub#7  
F  
40. (Twice Amended) A semiconductor device comprising a field effect transistor having an interface between a semiconductive silicon layer and a gate insulating layer, structurally characterized by the presence of deuterium at said interface resulting from post-fabrication passivation of said interface in a heated, deuterium gas-enriched atmosphere at a temperature of about 200°C to about 1000°C